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tion of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCOSURE STATEMENT BY APPLACANT (Use as many sheets as necessary)

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First Named Inventor Williams, Brett

Group Art Unit 2187

Examiner Name Kim, Hong DEC 1 9 2002

Sheet 1 of 1

Attorney Docket No: 303.164US3

Technology Center 2 100

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EXAMINER

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